General Description

OST75N65K7E2AF uses advanced Oriental-Semi's patented Trident-Gate Bipolar Transistor (TGBT™) technology to provide extremely low V_{CE}(sat), low gate charge, and excellent switching performance. This device is suitable for mid to high range switching frequency converters.

Features

- Advanced TGBT™ technology
- Excellent conduction and switching loss
- Excellent stability and uniformity
- AEC-Q101 Qualified for Automotive Application

AEC Qualified RoHS compliant

Applications

- Induction converters
- On-board charger

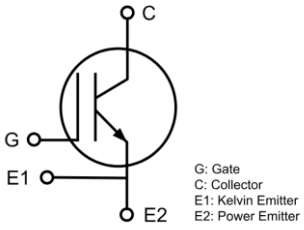
Key Performance Parameters

Parameter	Value	Unit
$V_{CES, min}$ @ 25°C	650	V
Maximum junction temperature	175	°C
$I_{C, pulse}$	300	A
$V_{CE(sat), typ}$ @ V_{GE}=15V	2.04	V
Q_g	96	nC

Marking Information

Product Name	Package	Marking
OST75N65K7E2AF	TO263-7L	OST75N65K7E2A

Package & Pin Information



Absolute Maximum Ratings at T_{vj}=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Collector emitter voltage	V_{CES}	650	V
Gate emitter voltage	V_{GES}	±20	V
Transient gate emitter voltage, T_P≤10μs, D<0.01		±30	V
Continuous collector current[1], T_C=25℃	I_C	90	A
Continuous collector current[1], T_C=100℃		75	A
Pulsed collector current[2], T_C=25℃	$I_{C,\ pulse}$	300	A
Power dissipation[3], T_C=25℃	P_D	300	W
Power dissipation[3], T_C=100℃		150	W
Operation and storage temperature	T_{stg}, T_{vj}	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
IGBT thermal resistance, junction-case	$R_{\theta JC}$	0.5	°C/W
Thermal resistance, junction-ambient[4]	$R_{\theta JA}$	40	°C/W

Electrical Characteristics at T_{vj}=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Collector-emitter breakdown voltage	$V_{(BR)CES}$	650			V	V_{GE}=0 V, I_C=0.5 mA
Collector-emitter saturation voltage	$V_{CE(sat)}$		2.04	2.3	V	V_{GE}=15 V, I_C=75 A T_{vj}=25°C
			2.93		V	V_{GE}=15 V, I_C=75 A, T_{vj} =125°C
			3.41		V	V_{GE}=15 V, I_C=75 A, T_{vj} =175°C
Gate-emitter threshold voltage	$V_{GE(th)}$	3.5	4.0	5.0	V	V_{CE}=V_{GE}, I_C=0.5 mA
Gate-emitter leakage current	I_{GES}			100	nA	V_{CE}=0 V, V_{GE}=20 V
Zero gate voltage collector current	I_{CES}			10	μA	V_{CE}=650 V, V_{GE}=0 V

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{ies}		5859		pF	V_{GE}=0 V, V_{CE}=25 V, f=100 kHz
Output capacitance	C_{oes}		75		pF	
Reverse transfer capacitance	C_{res}		4		pF	
Turn-on delay time	$t_{d(on)}$		31		ns	V_{GE}=15 V, V_{CC}=400 V, R_G=10 Ω, I_C=75 A
Rise time	t_r		21		ns	
Turn-off delay time	$t_{d(off)}$		83		ns	
Fall time	t_f		16		ns	
Turn-on energy	E_{on}		1.05		mJ	
Turn-off energy	E_{off}		0.48		mJ	
Turn-on delay time	$t_{d(on)}$		29		ns	V_{GE}=15 V, V_{CC}=400 V, R_G=10 Ω, I_C=30 A
Rise time	t_r		10		ns	
Turn-off delay time	$t_{d(off)}$		95		ns	
Fall time	t_f		16		ns	
Turn-on energy	E_{on}		0.21		mJ	
Turn-off energy	E_{off}		0.16		mJ	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		96		nC	V_{GE}=15 V, V_{CC}=520 V, I_C=75 A
Gate-emitter charge	Q_{ge}		39		nC	
Gate-collector charge	Q_{gc}		15		nC	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 inch^2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.

Electrical Characteristics Diagrams

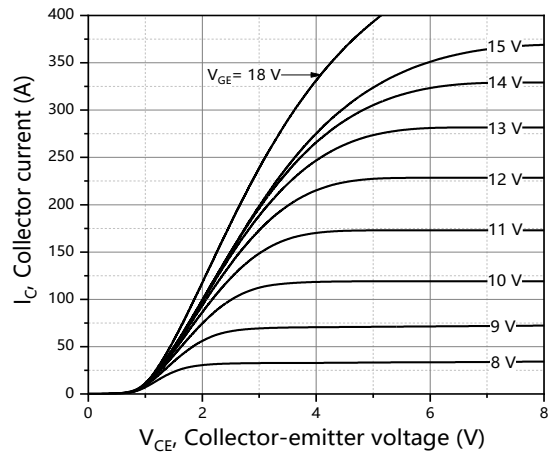


Figure 1. Typical output characteristics
(T_{vj}=25°C)

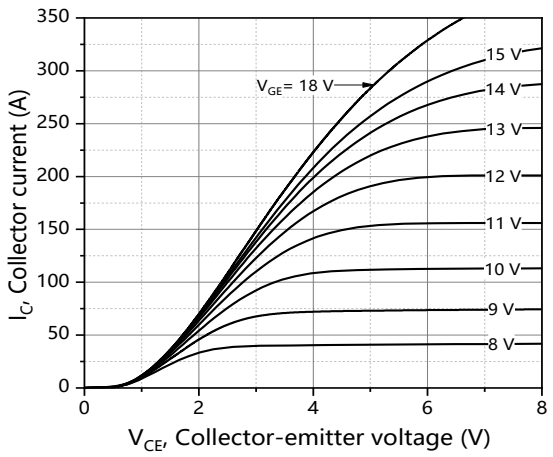


Figure 2. Typical output characteristics
(T_{vj}=150°C)

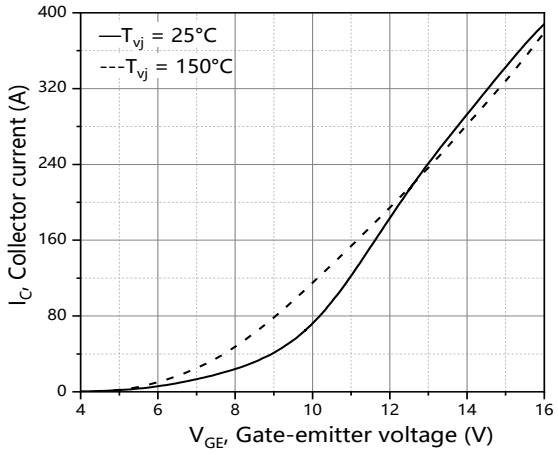


Figure 3. Typical transfer characteristics
(V_{CE}=20V)

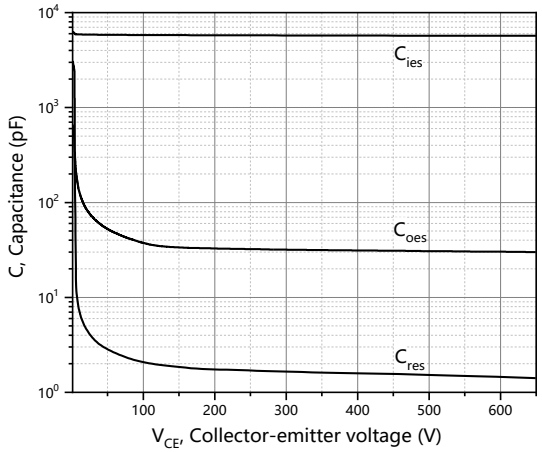


Figure 4. Typical capacitance
(V_{GE}=0V, f=100 kHz)

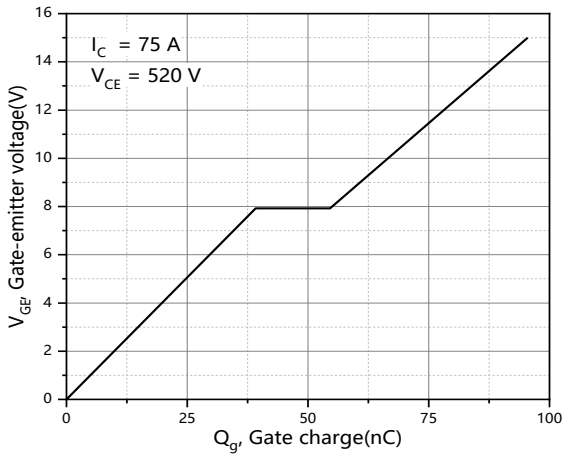


Figure 5. Typical gate charge

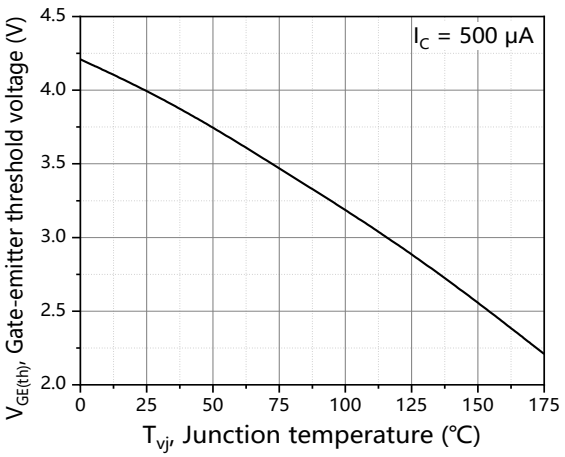


Figure 6. Gate-emitter threshold voltage

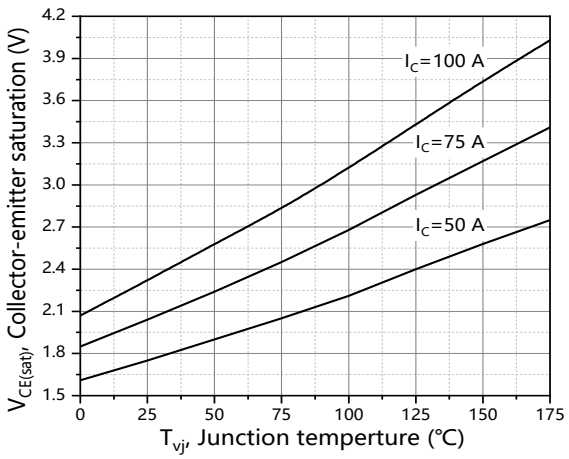


Figure 7. Typical collector-emitter voltage

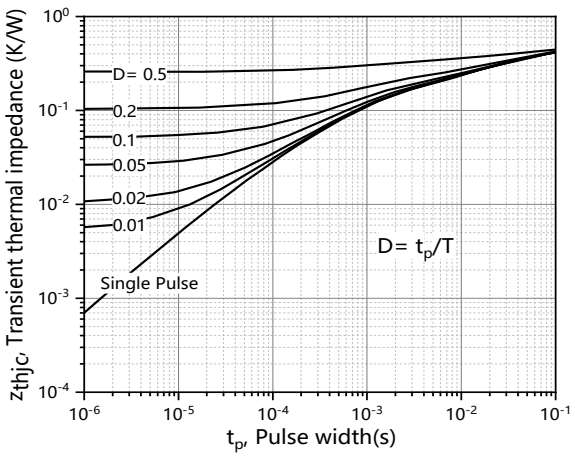


Figure 8. IGBT transient thermal impedance

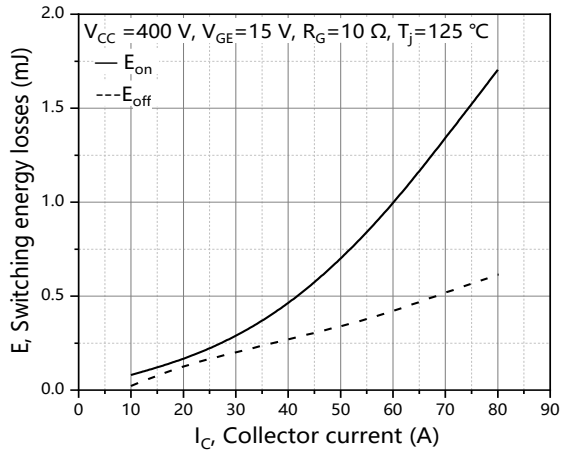
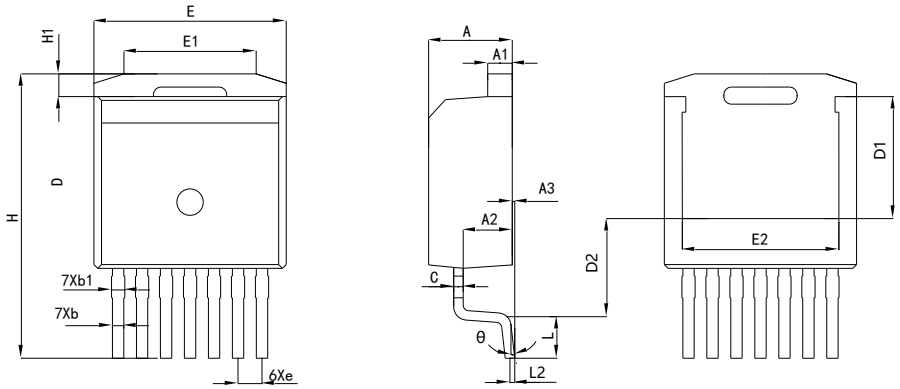


Figure 9. Switching energy vs. collector current

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.30	4.43	4.56
A1	1.20	1.30	1.40
A2	2.45	2.60	2.75
A3	0.00	0.13	0.25
b	0.50	0.60	0.70
b1	0.60	0.70	0.90
c	0.45	0.50	0.60
D	8.93	9.08	9.23
D1	6.30	6.45	6.60
D2	5.18 REF		
e	1.27 BSC		
E	10.08	10.18	10.28
E1	7.00 REF		
E2	7.90	8.30	8.70
H	14.53	15.03	15.53
H1	0.98	1.20	1.42
L	1.90	2.20	2.50
L2	0.25 BSC		
θ	0°	3°	7°

Version 1: TO263-7L-P package outline dimension

Ordering Information

Package Type	Units/ Reel	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO263-7L-P	800	1	800	5	4000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OST75N65K7E2AF	TO263-7L	yes	yes	yes

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